Preferred Devices

Thyristor Surge Protectors

High Voltage Bidirectional

NP Series Thyristor Surge Protector Devices (TSPD) protect telecommunication circuits such as central office, access, and customer premises equipment from overvoltage conditions. These are bidirectional devices so they are able to have functionality of 2 devices in one package, saving valuable space on board layout.

These devices will act as a crowbar when overvoltage occurs and will divert the energy away from circuit or device that is being protected.

Use of the NP Series in equipment will help meet various regulatory requirements including: GR-1089-CORE, IEC 61000-4-5, ITU K.20/21/45, IEC 60950, TIA-968-A, FCC Part 68, EN 60950, UL 1950.

ELECTRICAL PARAMETERS

	V _{DRM}	V _(BO)	V _T	I _{DRM}	I _(BO)	Ι _Τ	Ι _Η
Device	٧	٧	٧	μΑ	mA	Α	mA
NP0640SxT3G	58	77	4	5	800	2.2	150
NP0720SxT3G	65	88	4	5	800	2.2	150
NP0900SxT3G	75	98	4	5	800	2.2	150
NP1100SxT3G	90	130	4	5	800	2.2	150
NP1300SxT3G	120	160	4	5	800	2.2	150
NP1500SxT3G	140	180	4	5	800	2.2	150
NP1800SxT3G	170	220	4	5	800	2.2	150
NP2100SxT3G	180	240	4	5	800	2.2	150
NP2300SxT3G	190	260	4	5	800	2.2	150
NP2600SxT3G	220	300	4	5	800	2.2	150
NP3100SxT3G	275	350	4	5	800	2.2	150
NP3500SxT3G	320	400	4	5	800	2.2	150

G = indicates leadfree, RoHS compliant

SURGE DATA RATINGS

	Waveform		x = s			
Specification	Voltage μs	Current μs	Α	В	С	Unit
GR-1089-CORE	2x10	2x10	150	250	500	A(pk)
IEC 61000-4-5	1.2x50	8x20	150	250	400	
TIA-968-A	10x160	10x160	90	150	200	
GR-1089-CORE	10x360	10x360	75	125	175	
TIA-968-A	10x560	10x560	50	100	150	
ITU-T K.20/21	10x700	5x310	75	100	200	
GR-1089-CORE	10x1000	10x1000	50	80	100	

*N Recognized Components



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BIDIRECTIONAL SURFACE MOUNT THYRISTOR 64 – 350 VOLTS





SMB JEDEC DO-214AA CASE 403C

MARKING DIAGRAM



xxxx = Specific Device Code

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics (Note 1)	Symbol	Min	Тур	Max	Unit
Breakover Voltage (Both Polarities) NP0640SxT3G NP0720SxT3G NP0900SxT3G NP1100SxT3G NP11300SxT3G NP1500SxT3G NP1500SxT3G NP2300SxT3G NP2300SxT3G NP2600SxT3G NP2600SxT3G NP3100SxT3G NP3500SxT3G	V _(BO)			77 88 98 130 160 180 220 240 260 300 350 400	V
Off-State Voltage (Both Polarities) NP0640SxT3G NP0720SxT3G NP0900SxT3G NP1100SxT3G NP11300SxT3G NP1500SxT3G NP1500SxT3G NP2100SxT3G NP2300SxT3G NP2300SxT3G NP2600SxT3G NP2600SxT3G NP3500SxT3G NP3500SxT3G	V _{DRM}	58 65 75 90 120 140 170 180 190 220 275 320			V
Off State Current $(V_{D1} = 50 \text{ V})$ Both Polarities $(V_{D2} = V_{DRM})$ Both Polarities	I _{DRM1} I _{DRM2}			2.0 5.0	μ Α μ Α
Holding Current (Both Polarities) (Note 4) $V_S = 500 \text{ V}$; $I_T = 2.2 \text{ A}$	I _H	150	250	-	mA
On–State Voltage I_T = 1.0 A(pk) (PW = 300 μ Sec, DC = 2%)	V _T	-	-	4.0	V
Maximum Non–Repetitive Rate of Change of On–State Current (Note 1) (Haefely test method, 1.0 pk < 100 A)	di/dt	-	-	500	A/μSec
Critical Rate of Rise of Off–State Voltage (Linear Waveform, $V_D = 0.8 V_{DRM}$, $T_J = 25$ °C)	dv/dt	5.0	-	-	kV/μSec

CAPACITANCE

		Тур			
Characteristics	Symbol	Α	В	С	Unit
(f=1.0 MHz, 1.0 V _{rms} , 2 Vdc bias) NP0640SxT3G NP0720SxT3G NP0900SxT3G NP1100SxT3G NP1300SxT3G NP1500SxT3G	Co	70 70 70 70 70 60	125 125 125 125 100 100	210 210 210 210 210 180	pF
NP1800SxT3G NP2100SxT3G NP2300SxT3G NP2600SxT3G NP3100SxT3G NP3500SxT3G		60 60 40 40 40 40	100 100 60 60 60 60	180 180 100 100 100 100	

- Electrical parameters are based on pulsed test methods.
 di/dt must not be exceeded of a maximum of 100 A/μSec in this application.
 Measured under pulsed conditions to reduce heating
 Allow cooling before testing second polarity.

SURGE RATINGS

Characteristics		Α	В	С	Unit
Nominal Pulse Surge Short Circuit Current Non – Repetitive Double Exponential Decay Waveform (Notes 5, 6 and 7) 2 x 10 μSec 8 x 20 μSec 10 x 160 μSec 10 x 360 μSec 10 x 560 μSec 10 x 700 μSec 10 x 1000 μSec	IPPS1 IPPS2 IPPS3 IPPS4 IPPS5 IPPS6 IPPS7	150 150 90 75 50 75 50	250 250 150 125 100 100 80	500 400 200 150 150 200 100	A(pk)

- Allow cooling before testing second polarity.
 Measured under pulse conditions to reduce heating.
 Nominal values may not represent the maximum capability of a device.

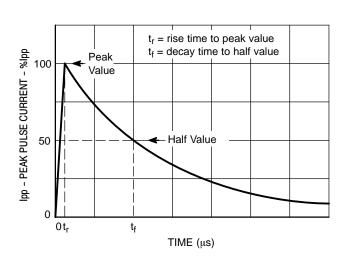


Figure 1. Exponential Decay Pulse Waveform

Symbol	Parameter			
V_{DRM}	Peak Off State Voltage			
V _(BO)	Breakover Voltage			
I _(BO)	Breakover Current			
I _H	Holding Current			
V _T	On State Voltage			
I _T	On State Current			

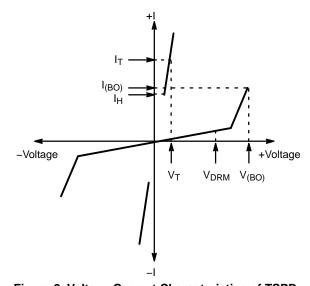


Figure 2. Voltage Current Characteristics of TSPD

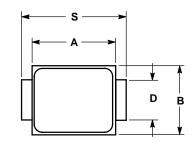
ORDERING INFORMATION

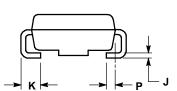
Part Number	Marking	Case	Shipping [†]				
NP0640SAT3G	064A						
NP0640SBT3G	064B						
NP0640SCT3G	064C						
NP0720SAT3G	072A						
NP0720SBT3G	072B						
NP0720SCT3G	072C						
NP0900SAT3G	090A						
NP0900SBT3G	090B						
NP0900SCT3G	090C						
NP1100SAT3G	110A						
NP1100SBT3G	110B						
NP1100SCT3G	110C						
NP1300SAT3G	130A						
NP1300SBT3G	130B						
NP1300SCT3G	130C						
NP1500SAT3G	150A						
NP1500SBT3G	150B						
NP1500SCT3G	150C	SMB	2502 / Tara and Basi				
NP1800SAT3G	180A	(Pb-Free)	2500 / Tape and Reel				
NP1800SBT3G	180B						
NP1800SCT3G	180C						
NP2100SAT3G	210A						
NP2100SBT3G	210B						
NP2100SCT3G	210C						
NP2300SAT3G	230A						
NP2300SBT3G	230B						
NP2300SCT3G	230C						
NP2600SAT3G	260A						
NP2600SBT3G	260B						
NP2600SCT3G	260C						
NP3100SAT3G	310A						
NP3100SBT3G	310B						
NP3100SCT3G	310C						
NP3500SAT3G	350A						
NP3500SBT3G	350B	7					
NP3500SCT3G	350C						

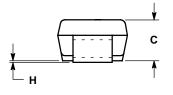
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SMB CASE 403C-01 ISSUE A





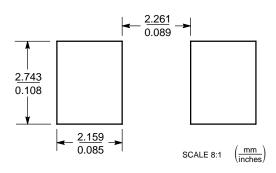


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.160	0.180	4.06	4.57	
В	0.130	0.150	3.30	3.81	
С	0.075	0.095	1.90	2.41	
D	0.077	0.083	1.96	2.11	
Н	0.0020	0.0060	0.051	0.152	
J	0.006	0.012	0.15	0.30	
K	0.030	0.050	0.76	1.27	
P	0.020 REF		0.51	REF	
S	0.205	0.220	5.21	5.59	

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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